

UNISONIC TECHNOLOGIES CO., LTD

25N10 **Power MOSFET**

N-CHANNEL ENHANCEMENT MODE POWER MOSFET

DESCRIPTION

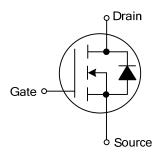
The UTC 25N10 is an N-channel enhancement mode power MOSFET and it uses UTC's perfect technology to provide designers with fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

It is generally suitable for all commercial-industrial applications and DC/DC converters requiring low voltage.

FEATURES

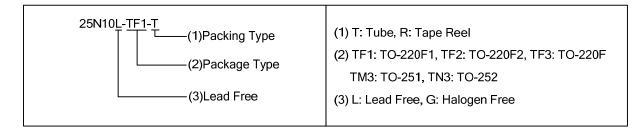
- * Single Drive Requirement
- * Low Gate Charge
- * RoHS Compliant

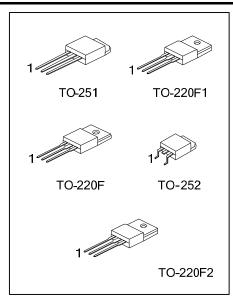
SYMBOL



ORDERING INFORMATION

Ordering Number		Deelsess	Pin Assignment			Deaking	
Lead Free Plating	Halogen Free	Package	1	2	3	Packing	
25N10L-TF1-T	25N10G-TF1-T	TO-220F1	G	D	S	Tube	
25N10L-TF2-T	25N10G-TF2-T	TO-220F2	G	D	S	Tube	
25N10L-TF3-T	25N10G-TF3-T	TO-220F	G	D	S	Tube	
25N10L-TM3-T	25N10G-TM3-T	TO-251	G	D	S	Tube	
25N10L-TN3-R	25N10G-TN3-R	TO-252	G	D	S	Tape Reel	





■ MARKING INFORMATION

PACKAGE	MARKING
TO-220F1 TO-220F2 TO-220 TO-251 TO-252	UTC 25N10 ☐

■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain Source Voltage		V_{DSS}	100	V	
Gate Source Voltage		V_{GSS}	±20	V	
Continuous Drain Current	T _C =25°C	I _D	23	Α	
(V _{GS} =10V)	T _C = 100°C	I _D	14.6	Α	
Pulsed Drain Current (Note 2)		I _{DM}	80	Α	
Total Power Dissipation (T _C =25°C)	TO-220F/TO-220F1		50		
	TO-220F2	P_{D}	52	W	
	TO-251/TO-252		41		
Operating Junction Temperature		TJ	-55 ~ +150	°C	
Storage Temperature		T _{STG}	-55 ~ +150	°C	

Note:1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT	
Junction to Ambient	TO-220F/TO-220F1 TO-220F2	θ_{JA}	62.5	°C/W	
	TO-251/TO-252		100		
Junction to Case	TO-220F/TO-220F1		2.5	°C/W	
	TO-220F2	θ_{JC}	2.4		
	TO-251/TO-252		3		

^{2.} Pulse width limited by max. junction temperature

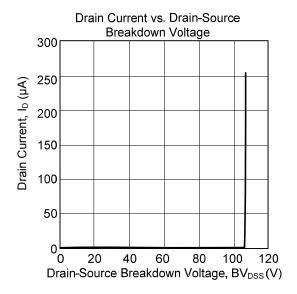
25N10

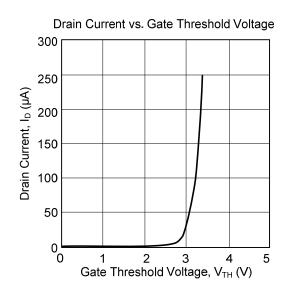
■ **ELECTRICAL CHARACTERISTICS** (T_J=25°C, unless otherwise specified)

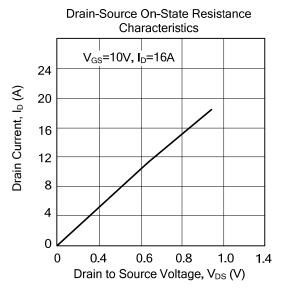
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PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNII	
OFF CHARACTERISTICS	 	<u> </u>	ı	1			
Orain-Source Breakdown Voltage BV _D		V_{GS} =0V, I_D =1mA	100			V	
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_{J}$	Reference to 25°C , I _D =1mA		0.14		V/°C	
Drain-Source Leakage Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V, T _J =25°C			25	μΑ	
Dialii-Source Leakage Current	IDSS	V _{DS} =80V, V _{GS} =0V,T _J =150°C			100	μΑ	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V			±100	nA	
ON CHARACTERISTICS			-				
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	2		4	V	
Static Drain-Source On-Resistance (Note)	R _{DS(ON)}	V _{GS} =10V, I _D =16A			80	mΩ	
Forward Transconductance	g FS	V _{DS} =10V, I _D =16A		14		S	
DYNAMIC PARAMETERS							
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1.0MHz		1060	1700	pF	
Output Capacitance	Coss			270		pF	
Reverse Transfer Capacitance	C _{RSS}			8		pF	
Gate Resistance	R_{G}			1.5	2.3	Ω	
SWITCHING PARAMETERS							
Total Gate Charge (Note)	Q_{G}			19	30	nC	
Gate Source Charge	Q_GS	V _{GS} =10V, V _{DS} =80V, I _D =16A		5		nC	
Gate Drain Charge	Q_GD	7		6		nC	
Turn-ON Delay Time ¹	t _{D(ON)}			10		ns	
Turn-ON Rise Time	t_R	V_{DD} =50V, I_{D} =16A, R_{G} =3.3 Ω ,		28		ns	
Turn-OFF Delay Time	t _{D(OFF)}	V_{GS} =10V, R_D =3.125 Ω		17		ns	
Turn-OFF Fall-Time	t₅			2		ns	
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Drain-Source Diode Forward Voltage (Note)	V _{SD}	I _S =16A, V _{GS} =0V			1.3	V	
Reverse Recovery Time	t _{RR}	I _S =16A,V _{GS} =0V,		90		ns	
Reverse Recovery Charge	Q_{RR}	dI/dt=100A/μs		380		nC	

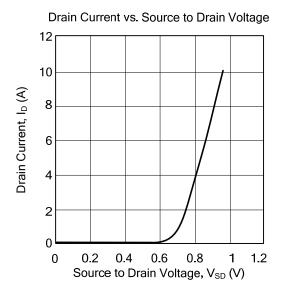
Note: Pulse Test : Pulse width \leq 300 μ s, Duty cycle \leq 2%.

■ TYPICAL CHARACTERISTICS









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